

REMARKS

Claims 1, 2, and 4-12 are all the claims pending in the application. Claims 3 and 13 through 22 are cancelled herein without prejudice or disclaimer. Claims 1, 6, and 8 are amended herein. Applicants gratefully acknowledge that claim 8-12 have been allowed and that claims 3, 4, and 6 would be allowable if rewritten in independent form including all of the limitations of the base claims and any intervening claims. Claims 1-2, 5 and 7, stand rejected on prior art grounds. Applicants respectfully traverse these rejections based on the following discussion.

I. The Prior Art Rejections

Claims 1-2, 5 and 7 stand rejected under 35 U.S.C. §102(b) as being anticipated by Lee, et al. (U.S. Patent No. 6,190,954), hereinafter referred to as "Lee". Applicants respectfully traverse these rejections based on the following discussion.

Lee teaches a method to provide for more robust latchup-immune CMOS transistors by increasing the breakover voltage V_{BO} , or trigger point, of the parasitic npn and pnp transistors present in CMOS structures. These goals are achieved by adding a barrier layer to both the n-well and p-well of a twin-well CMOS structure, thus increasing the energy gap for electrons and holes of the parasitic npn and pnp transistor, respectively.

The claimed invention, as provided in amended independent claim 1 includes the limitations of original dependent claim 3 (now cancelled without prejudice or disclaimer), which the Office Action indicates includes allowable subject matter, thereby making amended independent claim 1 patentably distinguishable from the prior art references of

record. Specifically, independent claim 1 provides, in part, "...a shallow trench isolation region, wherein said trench structure comprises a deep trench structure having a depth and a width, wherein said depth is at least twice as large as said width, and wherein said shallow trench isolation region is over said deep trench structure...." As admitted in the Office Action (pages 3 and 4), these features are neither taught or suggested or rendered obvious by the prior art of record. Hence, amended independent claim 1 and dependent claims 2 and 4 through 7, by dependency, are in condition for immediate allowance.

Moreover, the Applicants note that all claims are properly supported in the specification and accompanying drawings, and no new matter is being added. In view of the foregoing, the Examiner is respectfully requested to reconsider and withdraw the rejections.

II. Formal Matters and Conclusion

With respect to the rejections to the claims, the claims have been amended, above, to overcome these rejections. In view of the foregoing, the Examiner is respectfully requested to reconsider and withdraw the rejections to the claims.

In view of the foregoing, Applicants submit that claims 1, 2, and 4-12, all the claims presently pending in the application, are patentably distinct from the prior art of record and are in condition for allowance. The Examiner is respectfully requested to pass the above application to issue at the earliest possible time.

Should the Examiner find the application to be other than in condition for allowance, the Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary. Please charge any

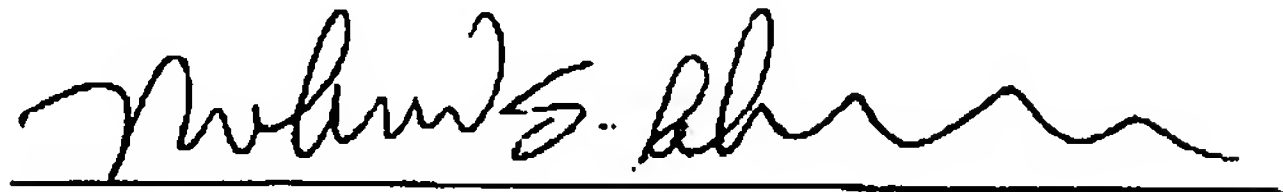
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deficiencies and credit any overpayments to Attorney's Deposit Account Number 09-0456.

Respectfully submitted,

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